

**AMENDMENTS TO THE CLAIMS**

1. (Previously Presented) A method of fabricating a pixel electrode in a liquid crystal display including a switching device for driving the pixel electrode, the method comprising:  
depositing a protective film over a substrate to cover the switching device;  
defining a contact hole in the protective film to expose one electrode of the switching device; and  
forming the pixel electrode connected, via the contact hole, to said one exposed electrode, wherein the pixel electrode is formed by placing the substrate in a vacuum chamber and injecting hydrogen-containing gas at a temperature of less than about 400 °C, wherein the substrate has a temperature between about 50 °C and about 150 °C when forming the pixel electrode, the substrate temperature being half said less than about 400 °C temperature and the pixel electrode has an amorphous structure.

2. (Canceled)

3. (Original) The method as claimed in claim 1, wherein the pixel electrode is etched with a weak acid etchant.

4-5. (Canceled)

6. (Original) The method as claimed in claim 1, further comprising the steps of:

forming a gate electrode over the substrate;

entirely depositing a gate insulating film over the substrate to cover the gate electrode;  
and

continuously depositing an active layer and an ohmic contact layer to overlap the gate  
electrode.

7. (Original) The method as claimed in claim 1, wherein the protective layer is a  
passivation layer.

8. (Original) The method as claimed in claim 7, wherein the passivation layer is made  
from an inorganic insulation material or an organic insulation material.

9. (Original) The method as claimed in claim 7, wherein the passivation layer is at least  
one material selected from the group consisting of silicon nitride, silicon oxide, an acrylic,  
polytetrafluoroethylene, benzocyclobutene, fluoropolymer resin and perfluorocyclobutane.

10. (Original) The method as claimed in claim 1, wherein the pixel electrode comprises a  
transparent conductive material.

11. (Original) The method as claimed in claim 1, wherein the pixel electrode comprises at  
least one material selected from the group consisting of indium tin oxide, tin oxide and indium  
zinc oxide.

12. (Original) The method as claimed in claim 1, wherein the switching device has source and drain electrodes, and the source and drain electrodes comprise at least one material selected from the group consisting of Mo, Cr, Ti, Ta, MoW, MoTa and MoNb.

13. (Previously Presented) A pixel electrode in a liquid crystal display, which comprises:  
a substrate;  
a switching device over the substrate;  
a protective film over a substrate covering the switching device; and  
a contact hole in the protective film, the contact hole exposing one electrode of the switching device, the pixel electrode being connected, via the contact hole, to said one exposed electrode, wherein the pixel electrode is formed by placing the substrate in a vacuum chamber and injecting hydrogen-containing gas at a temperature of less than about 400 °C, wherein the substrate has a temperature between about 50 °C and 150 °C when forming the pixel electrode, the substrate temperature being half said less than about 400 °C temperature and the pixel electrode has an amorphous structure.

14. (Canceled)

15. (Original) The pixel electrode as claimed in claim 13, which further comprises:  
a gate electrode over the substrate;  
a gate insulating film over the substrate covering the gate electrode; and  
an active layer and an ohmic contact layer overlapping the gate electrode.

16. (Original) The pixel electrode as claimed in claim 13, wherein the protective layer is an organic or inorganic passivation layer formed from at least one material selected from the group consisting of silicon nitride, silicon oxide, an acrylic, polytetrafluoroethylene, benzocyclobutene, fluoropolymer resin and perfluorocyclobutane.

17. (Original) The pixel electrode as claimed in claim 13, wherein the pixel electrode comprises a transparent conductive material selected from the group consisting of indium tin oxide, tin oxide and indium zinc oxide.

18. (Original) The pixel electrode as claimed in claim 13, wherein the switching device has source and drain electrodes, and the source and drain electrodes comprise at least one material selected from the group consisting of Mo, Cr, Ti, Ta, MoW, MoTa and MoNb.

19-23. (Canceled)